

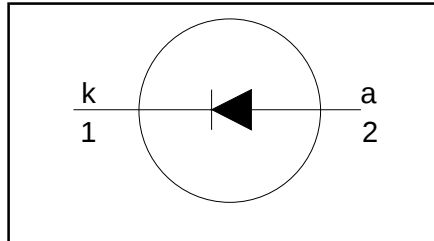
Rectifier diodes ultrafast

BYV29 series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 300 \text{ V} / 400 \text{ V} / 500 \text{ V}$$

$$V_F \leq 1.03 \text{ V}$$

$$I_{F(AV)} = 9 \text{ A}$$

$$t_{rr} \leq 60 \text{ ns}$$

GENERAL DESCRIPTION

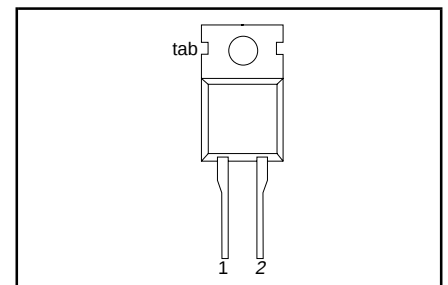
Ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV29 series is supplied in the conventional leaded SOD59 (TO220AC) package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode
tab	cathode

SOD59 (TO220AC)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V_{RRM}	Peak repetitive reverse voltage	BYV29 square wave; $\delta = 0.5$; $T_{mb} \leq 123^\circ\text{C}$ $t = 25 \mu\text{s}$; $\delta = 0.5$; $T_{mb} \leq 123^\circ\text{C}$ $t = 10 \text{ ms}$ $t = 8.3 \text{ ms}$ sinusoidal; with reappplied $V_{RRM(max)}$	-	-300	-400	-500	V
V_{RWM}	Crest working reverse voltage		-	300	400	500	V
V_R	Continuous reverse voltage		-	300	400	500	V
$I_{F(AV)}$	Average forward current ¹		-	9			A
I_{FRM}	Repetitive peak forward current		-	18			A
I_{FSM}	Non-repetitive peak forward current.		-	100			A
			-	110			A
T_{stg}	Storage temperature		-40	150			$^\circ\text{C}$
T_j	Operating junction temperature		-	150			$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$	Thermal resistance junction to mounting base	in free air.	-	-	2.5	K/W
$R_{th j-a}$	Thermal resistance junction to ambient		-	60	-	K/W

¹ Neglecting switching and reverse current losses.

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ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	I _F = 8 A; T _j = 150 °C	-	0.90	1.03	V
		I _F = 8 A	-	1.05	1.25	V
		I _F = 20 A	-	1.20	1.40	V
I _R	Reverse current	V _R = V _{RRM}	-	2.0	50	μA
		V _R = V _{RRM} ; T _j = 100 °C	-	0.1	0.35	mA
Q _s	Reverse recovery charge	I _F = 2 A to V _R ≥ 30 V; dI _F /dt = 20 A/μs	-	40	60	nC
t _{rr}	Reverse recovery time	I _F = 1 A to V _R ≥ 30 V; dI _F /dt = 100 A/μs	-	50	60	ns
I _{rrm}	Peak reverse recovery current	I _F = 10 A to V _R ≥ 30 V; dI _F /dt = 50 A/μs; T _j = 100 °C	-	4.0	5.5	A
V _{fr}	Forward recovery voltage	I _F = 10 A; dI _F /dt = 10 A/μs	-	2.5	-	V

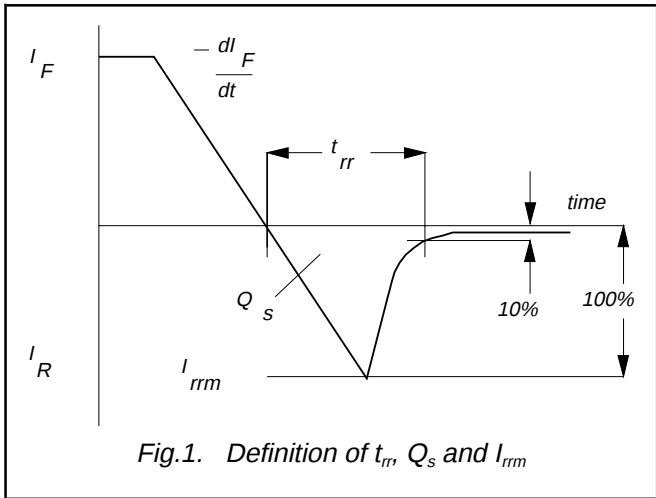


Fig.1. Definition of t_{rr}, Q_s and I_{rrm}

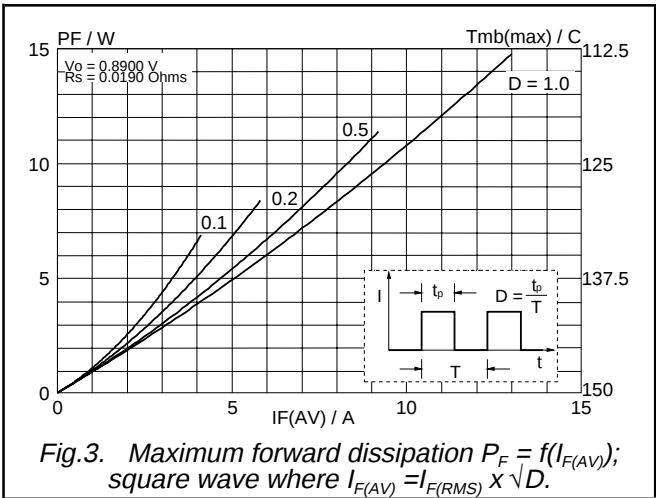


Fig.3. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square wave where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

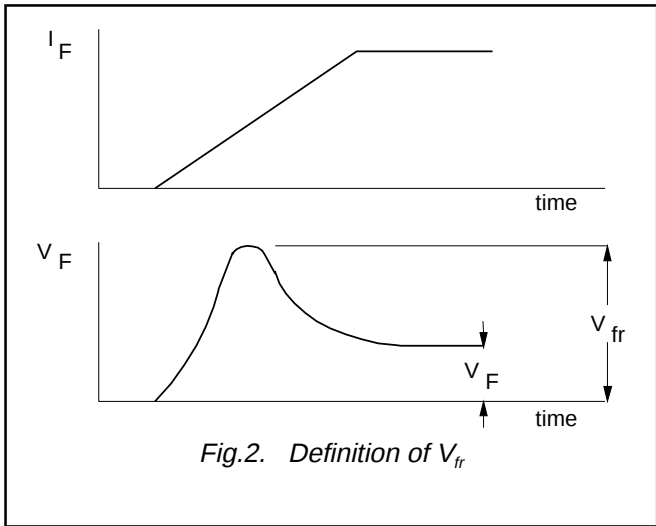


Fig.2. Definition of V_{fr}

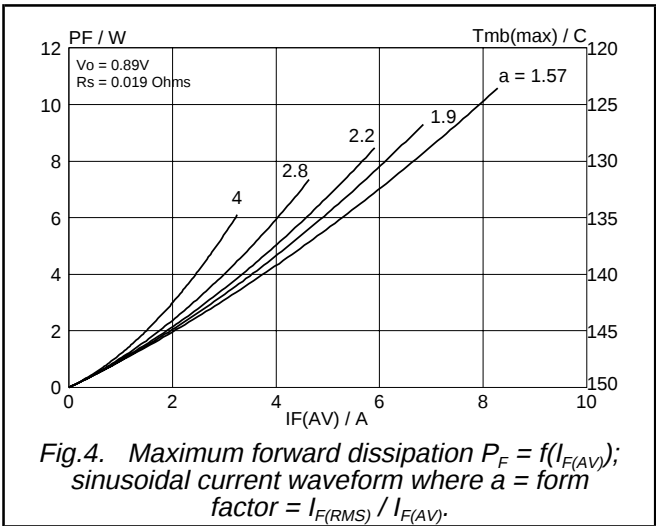
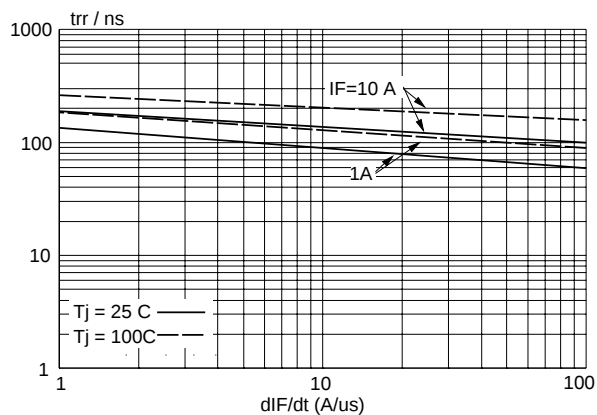
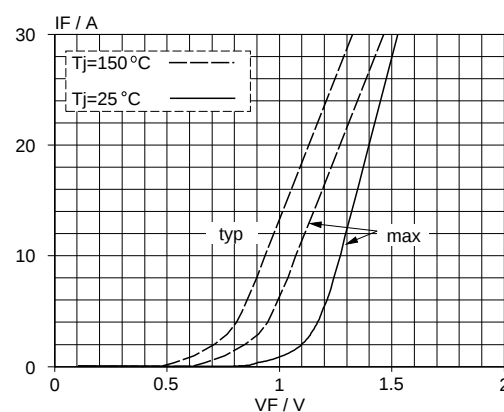
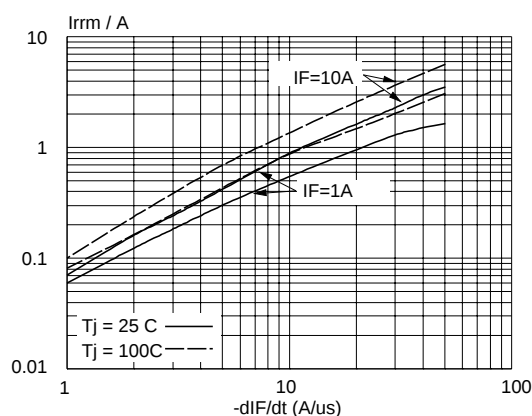
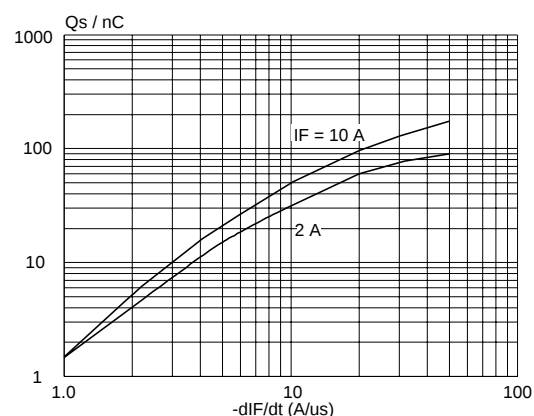
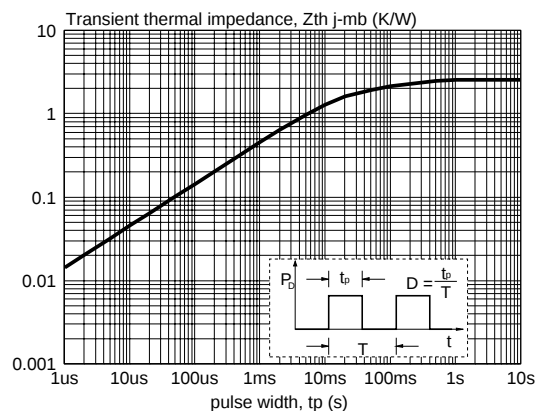


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$.

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Fig.5. Maximum t_{rr} at $T_j = 25^\circ\text{C}$ and 100°C Fig.7. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j Fig.6. Maximum I_{rrm} at $T_j = 25^\circ\text{C}$ and 100°C .Fig.8. Maximum Q_s at $T_j = 25^\circ\text{C}$ Fig.9. Transient thermal impedance $Z_{th\ j-mb} = f(t_p)$

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

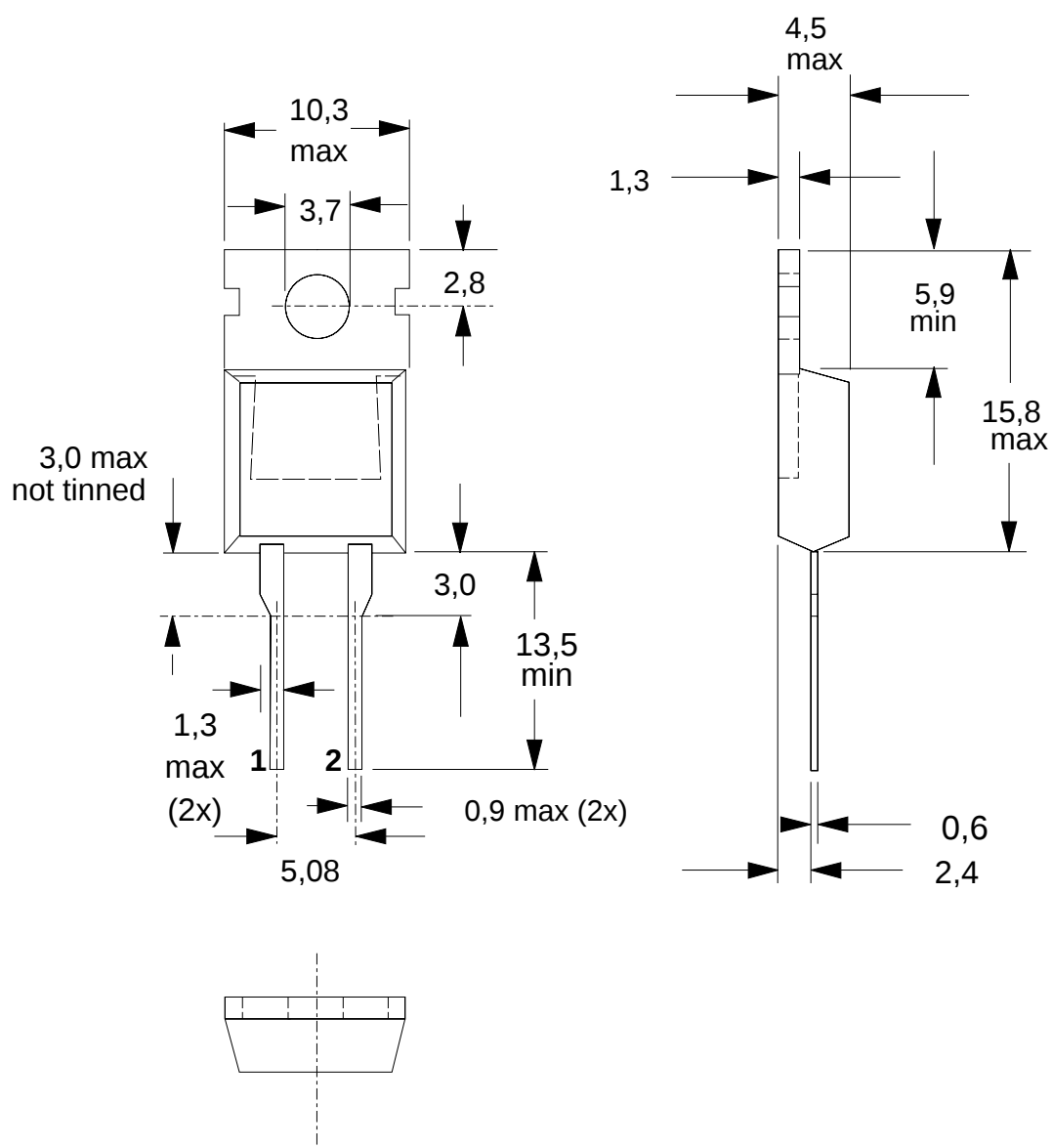


Fig.10. SOD59 (TO220AC). pin 1 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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